

General Description

The WSR180N10 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSR180N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

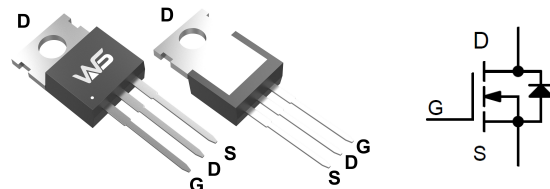
Product Summary

| BV_{DSS} | $R_{DS(on)}$ | I_D |
|------------|---------------|-------|
| 100V | 3.0m Ω | 180A |

Applications

- Power Management in TV Converter.
- DC-DC Converter
- LED TV Back Light

TO-220AB Pin Configuration



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|-----------------------|--|------------|------------|
| V_{DS} | Drain-Source Voltage | 100 | V |
| V_{GS} | Gate-Source Voltage | ± 25 | V |
| $I_D@T_C=25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^1$ | 180 | A |
| $I_D@T_C=100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V^1$ | 90 | A |
| I_{DM} | Pulsed Drain Current ² , $T_C=25^\circ C$ | 600 | A |
| EAS | Avalanche Energy, Single pulse | 545 | mJ |
| I_{AS} | Avalanche Current, Single pulse | 60 | A |
| $P_D@T_C=25^\circ C$ | Total Power Dissipation ⁴ | 225 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | 150 | $^\circ C$ |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|--|------|------|--------------|
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient ¹ | --- | 50 | $^\circ C/W$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case ¹ | --- | 0.55 | $^\circ C/W$ |

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|--|---|------|-------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250μA | 100 | --- | --- | V |
| ΔBV _{DSS} /ΔT _J | BV _{DSS} Temperature Coefficient | Reference to 25°C, I _D =1mA | --- | 0.096 | --- | V/°C |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =10V, I _D =80A | --- | 3.0 | 4.0 | mΩ |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250μA | 2.5 | 3.0 | 4.5 | V |
| ΔV _{GS(th)} | V _{GS(th)} Temperature Coefficient | | --- | -5.5 | --- | mV/°C |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =80V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | μA |
| | | V _{DS} =80V, V _{GS} =0V, T _J =55°C | --- | --- | 5 | |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V, V _{DS} =0V | --- | --- | ±100 | nA |
| g _{fs} | Forward Transconductance | V _{DS} =5V, I _D =50A | --- | 120 | --- | S |
| R _g | Gate Resistance | V _{DS} =0V, V _{GS} =0V, f=1MHz | --- | 0.7 | 1.5 | Ω |
| Q _g | Total Gate Charge (10V) | V _{DS} =80V, V _{GS} =10V, I _D =80A | --- | 80 | --- | nC |
| Q _{gs} | Gate-Source Charge | | --- | 33 | --- | |
| Q _{gd} | Gate-Drain Charge | | --- | 18 | --- | |
| T _{d(on)} | Turn-On Delay Time | V _{DD} =50V, V _{GS} =10V, R _G =5Ω, I _D =80A | --- | 28 | --- | ns |
| T _r | Rise Time | | --- | 55 | --- | |
| T _{d(off)} | Turn-Off Delay Time | | --- | 98 | --- | |
| T _f | Fall Time | | --- | 24 | --- | |
| C _{iss} | Input Capacitance | V _{DS} =50V, V _{GS} =0V, f=1MHz | --- | 4120 | --- | pF |
| C _{oss} | Output Capacitance | | --- | 1250 | --- | |
| C _{rss} | Reverse Transfer Capacitance | | --- | 65 | --- | |

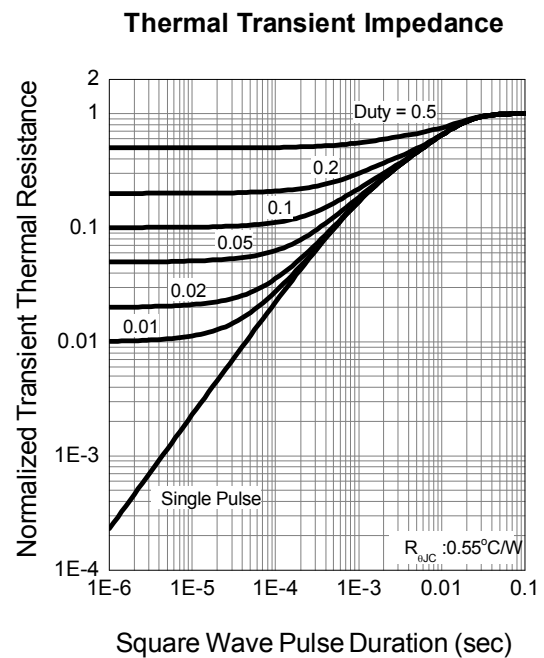
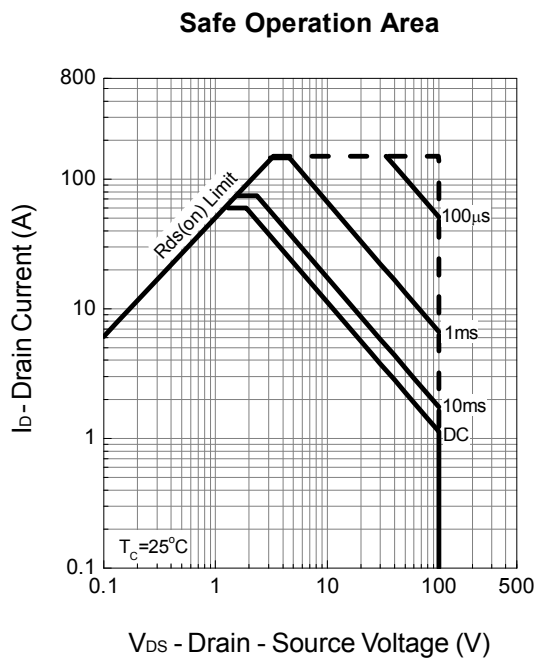
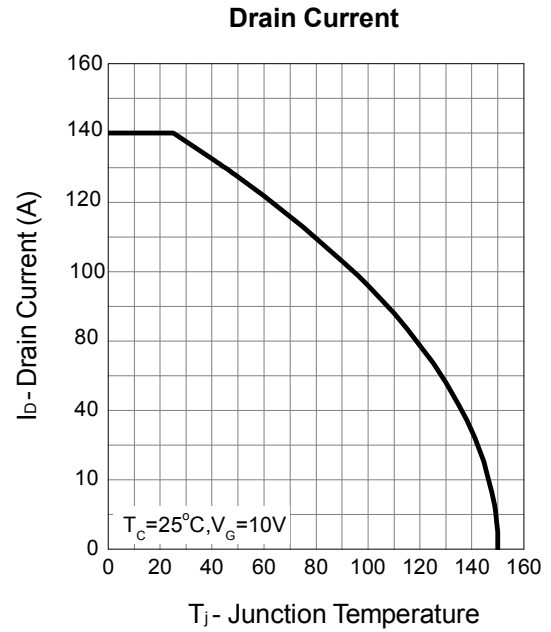
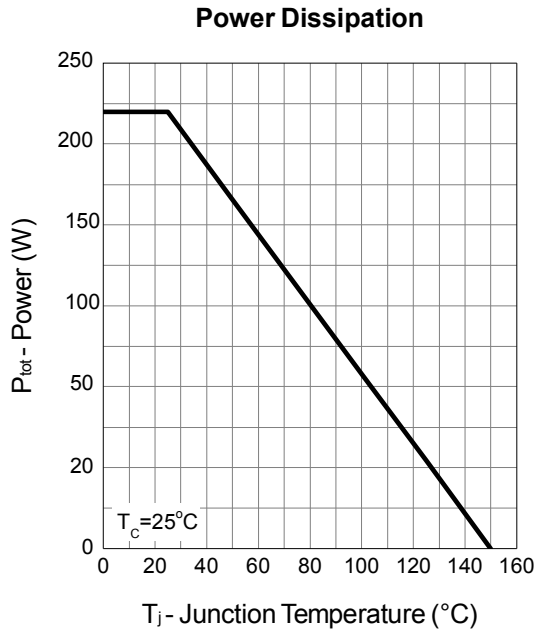
Diode Characteristics

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-----------------|--|--|------|------|------|------|
| I _S | Continuous Source Current ^{1,6} | V _G =V _D =0V, Force Current | --- | --- | 80 | A |
| V _{SD} | Diode Forward Voltage ² | V _{GS} =0V, I _S =50A, T _J =25°C | --- | 0.8 | 1.3 | V |
| t _{rr} | Reverse Recovery Time | I _F =50A, dI/dt=100A/μs, T _J =25°C | --- | 85 | --- | nS |
| Q _{rr} | Reverse Recovery Charge | | --- | 200 | --- | nC |

Note :

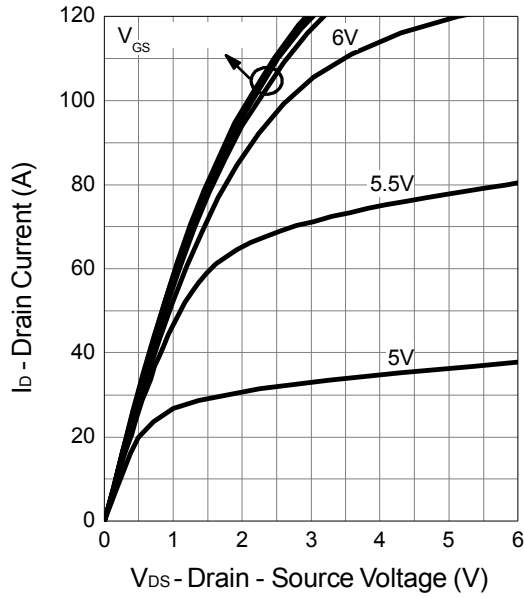
1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10sec.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V_{DS}=80V, V_{GS}=10V, L=0.1mH,
4. The power dissipation is limited by 150°C junction temperature
5. The Min. value is 100% EAS tested guarantee.
6. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Operating Characteristics

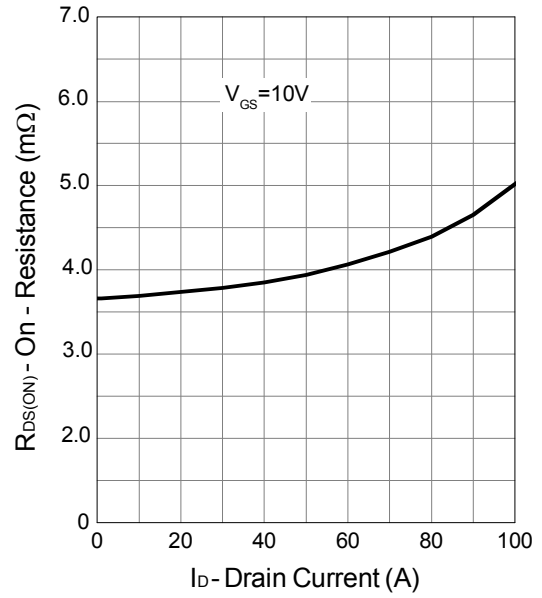


Typical Operating Characteristics (Cont.)

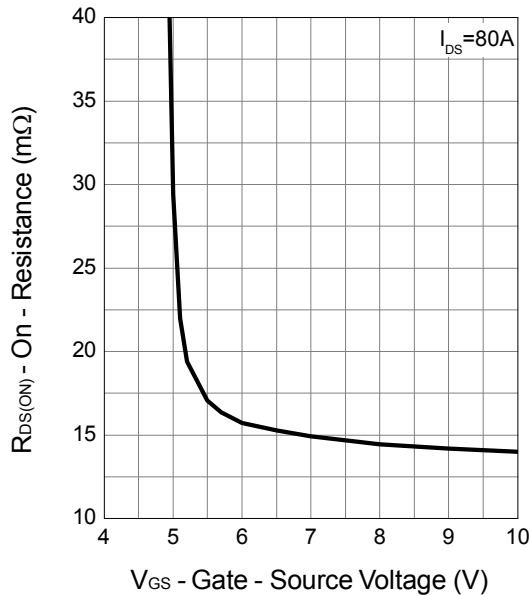
Output Characteristics



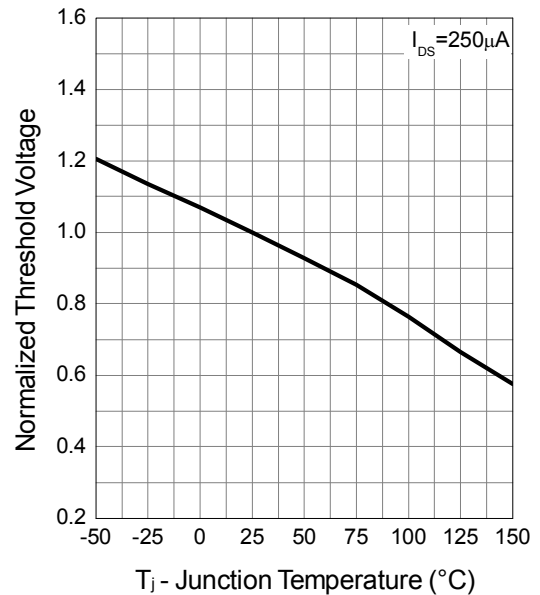
Drain-Source On Resistance



Gate-Source On Resistance

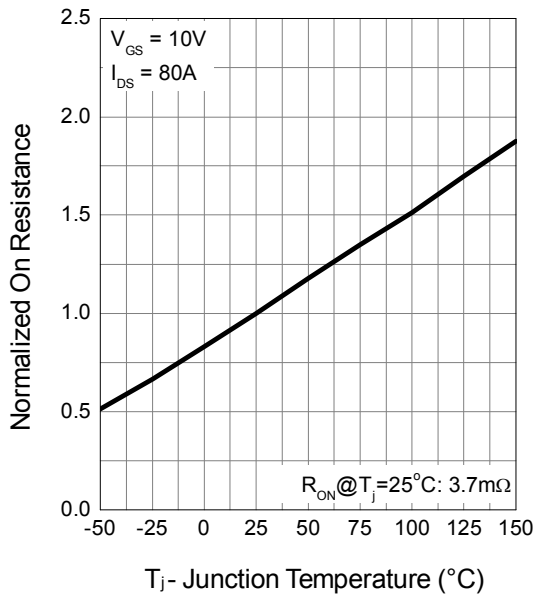


Gate Threshold Voltage

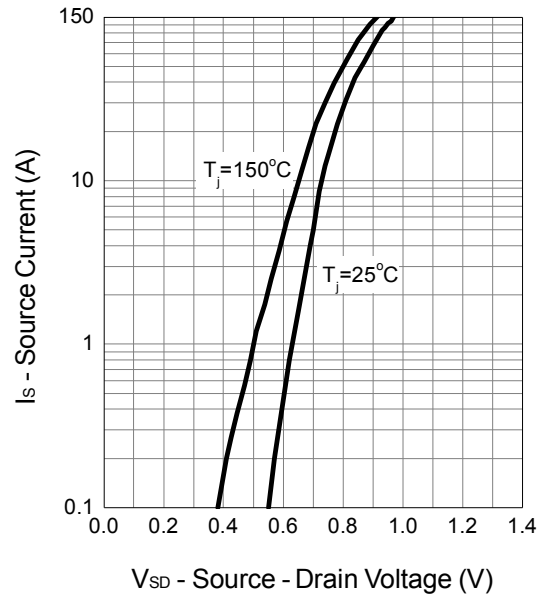


Typical Operating Characteristics (Cont.)

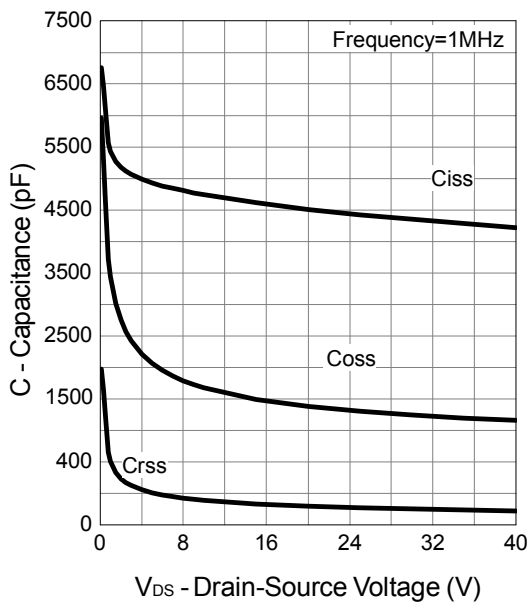
Drain-Source On Resistance



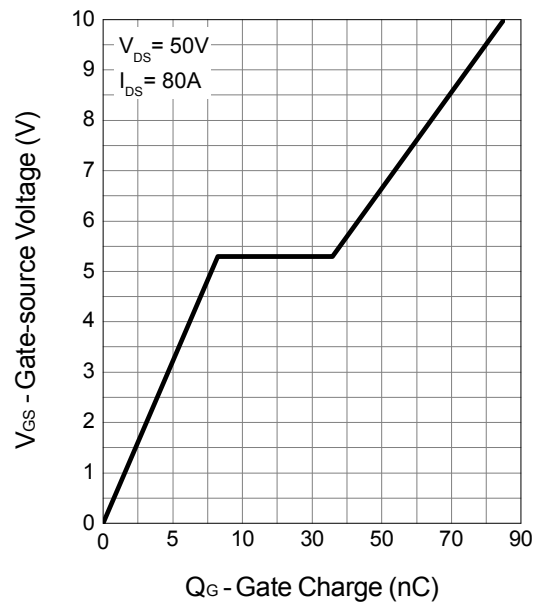
Source-Drain Diode Forward

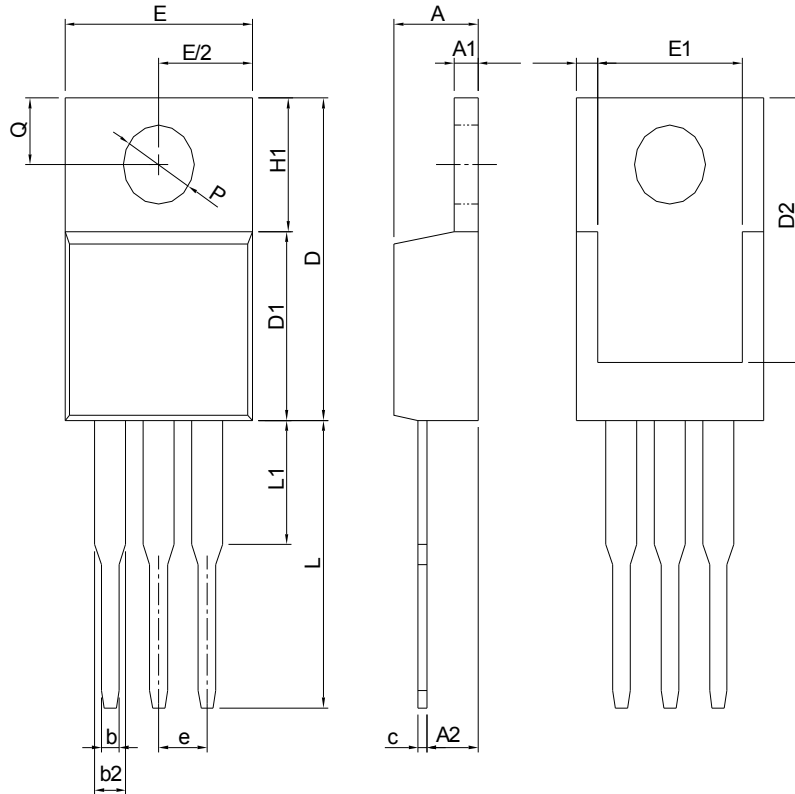


Capacitance

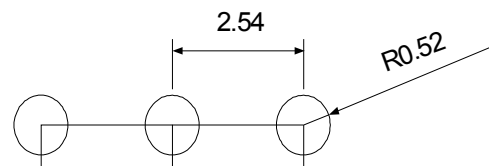


Gate Charge



Package Information TO-220AB


| DIMENSIONS | TO-220 | | | |
|------------|-------------|-------|-----------|-------|
| | MILLIMETERS | | INCHES | |
| | MIN. | MAX. | MIN. | MAX. |
| A | 3.56 | 4.83 | 0.140 | 0.190 |
| A1 | 0.51 | 1.40 | 0.020 | 0.055 |
| A2 | 2.03 | 2.92 | 0.080 | 0.115 |
| b | 0.38 | 1.02 | 0.015 | 0.040 |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.22 | 16.51 | 0.560 | 0.650 |
| D1 | 8.38 | 9.02 | 0.330 | 0.355 |
| D2 | 12.19 | 13.65 | 0.480 | 0.537 |
| E | 9.65 | 10.67 | 0.380 | 0.420 |
| E1 | 6.86 | 8.89 | 0.270 | 0.350 |
| e | 2.54 BSC | | 0.100 BSC | |
| H1 | 5.84 | 6.86 | 0.230 | 0.270 |
| L | 12.70 | 14.73 | 0.500 | 0.580 |
| L1 | | 6.35 | | 0.250 |
| P | 3.53 | 4.09 | 0.139 | 0.161 |
| Q | 2.54 | 3.43 | 0.100 | 0.135 |

RECOMMENDED LAND PATTERN


UNIT: mm



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